

FFP08S60S



Features

- Stealth Recovery $t_{rr} = 30 \text{ ns}$ (@ $I_F = 8 \text{ A}$)
- Max Forward Voltage, $V_F = 2.6 \text{ V}$ (@ $T_C = 25^\circ\text{C}$)
- 600V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

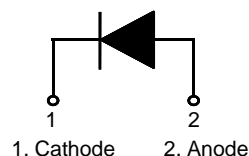
8 A, 600 V, STEALTH™ II Diode

The FFP08S60S is a STEALTH™ II diode with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction. This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Applications

- General Purpose
- Switching Mode Power Supply
- Boost Diode in Continuous Mode Power Factor Corrections
- Power Switching Circuits

Pin Assignments



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Unit |
|----------------|---|--------------|------------------|
| V_{RRM} | Peak Repetitive Reverse Voltage | 600 | V |
| V_{RWM} | Working Peak Reverse Voltage | 600 | V |
| V_R | DC Blocking Voltage | 600 | V |
| $I_{F(AV)}$ | Average Rectified Forward Current @ $T_C = 115^\circ\text{C}$ | 8 | A |
| I_{FSM} | Non-repetitive Peak Surge Current 60Hz Single Half-Sine Wave | 80 | A |
| T_J, T_{STG} | Operating Junction and Storage Temperature | - 65 to +150 | $^\circ\text{C}$ |

Thermal Characteristics

| Symbol | Parameter | Max | Unit |
|-----------------|--|-----|--------------------|
| $R_{\theta JC}$ | Maximum Thermal Resistance, Junction to Case | 2.5 | $^\circ\text{C/W}$ |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|-------------|-----------|-----------|------------|----------|
| F08S60S | FFP08S60STU | TO-220-2L | - | - | 50 |

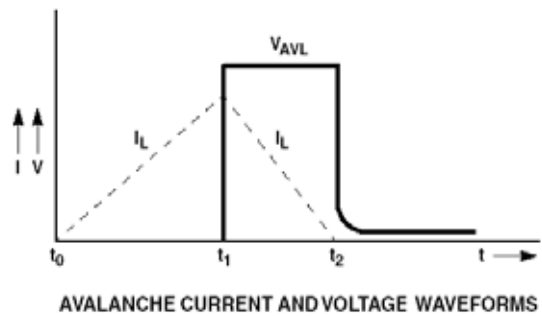
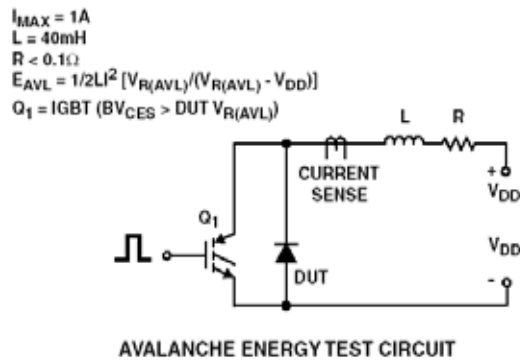
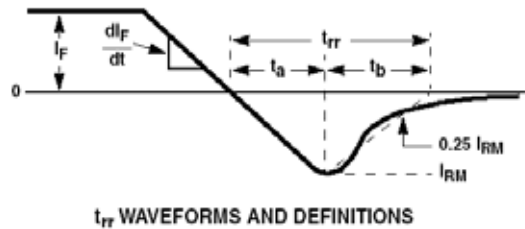
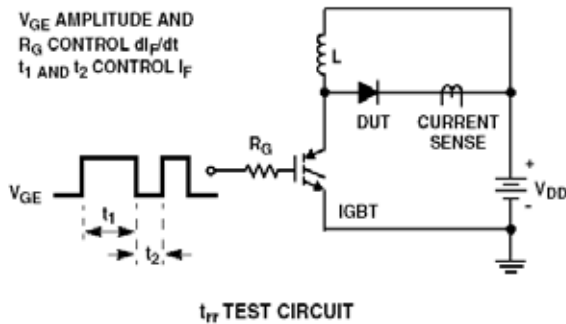
Electrical Characteristics T_C = 25°C unless otherwise noted

| Parameter | Conditions | Min. | Typ. | Max | Unit |
|-----------------------------|--|------|------|-----|------|
| V _F ¹ | I _F = 8 A | - | 2.1 | 2.6 | V |
| | I _F = 8 A | - | 1.6 | - | V |
| I _R ¹ | V _R = 600 V | - | - | 100 | μA |
| | V _R = 600 V | - | - | 500 | μA |
| t _{rr} | I _F = 1 A, di/dt = 100 A/μs, V _R = 30 V | - | - | 25 | ns |
| trr | I _F = 8 A, di/dt = 200 A/μs, V _R = 390 V | - | 19 | 30 | ns |
| I _{rr} | | - | 2.2 | - | A |
| S factor | | - | 0.6 | - | - |
| Q _{rr} | | - | 21 | - | nC |
| trr | | - | 58 | - | ns |
| I _{rr} | - | 4.3 | - | A | |
| S factor | - | 1.3 | - | - | |
| Q _{rr} | - | 125 | - | nC | |
| W _{AVL} | Avalanche Energy (L = 40 mH) | 20 | - | - | mJ |

Notes:

1. Pulse : Test Pulse width = 300 μs, Duty Cycle = 2%

Test Circuit and Waveforms



Typical Performance Characteristics $T_c = 25^\circ\text{C}$ unless otherwise noted

Figure 1. Typical Forward Voltage Drop

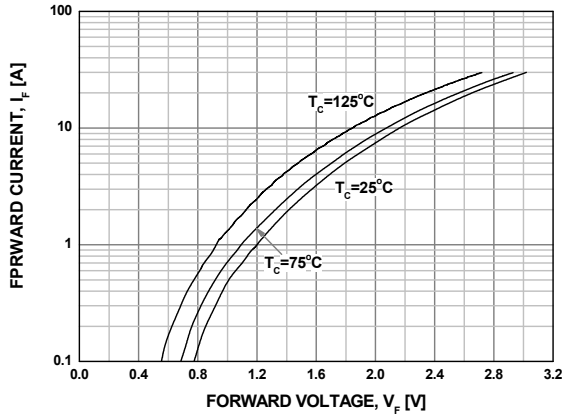


Figure 2. Typical Reverse Current

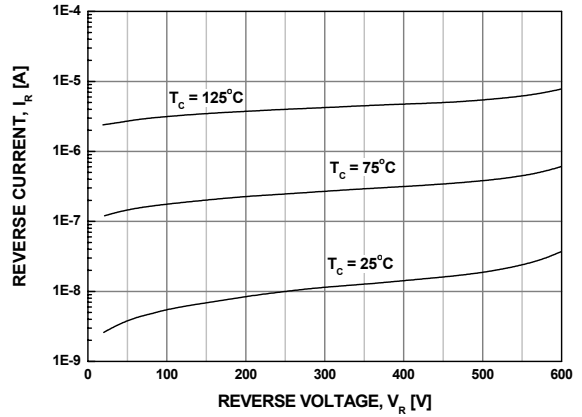


Figure 3. Typical Junction Capacitance

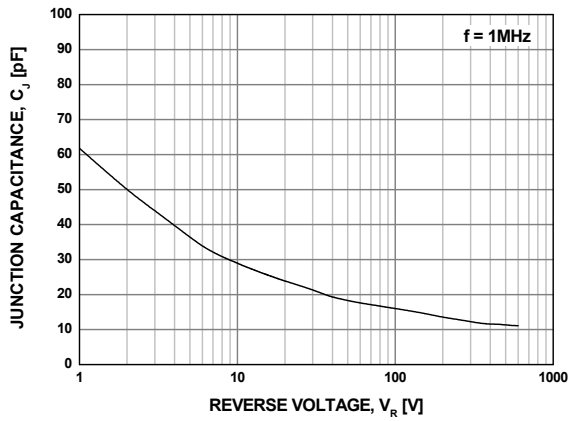


Figure 4. Typical Reverse Recovery Time

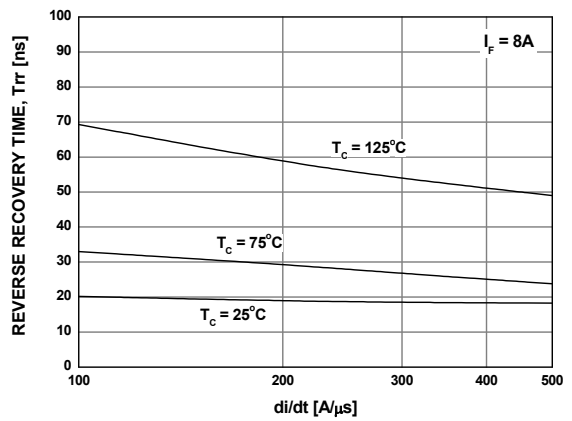


Figure 5. Typical Reverse Recovery Current

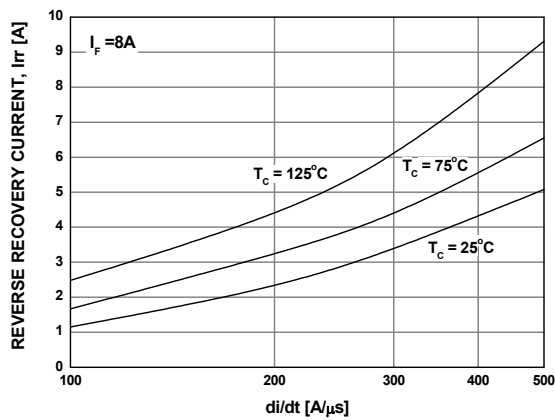
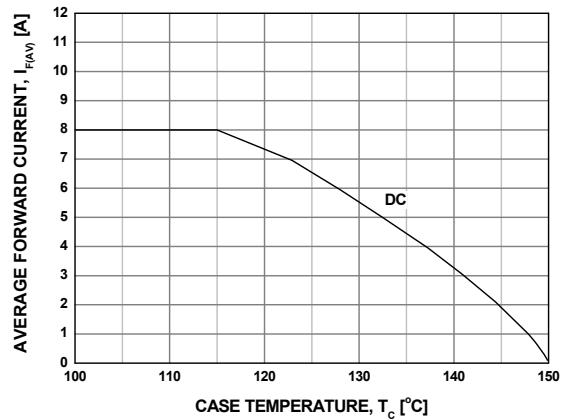
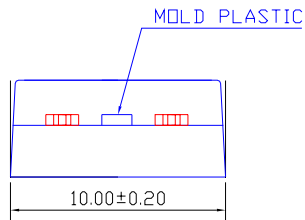
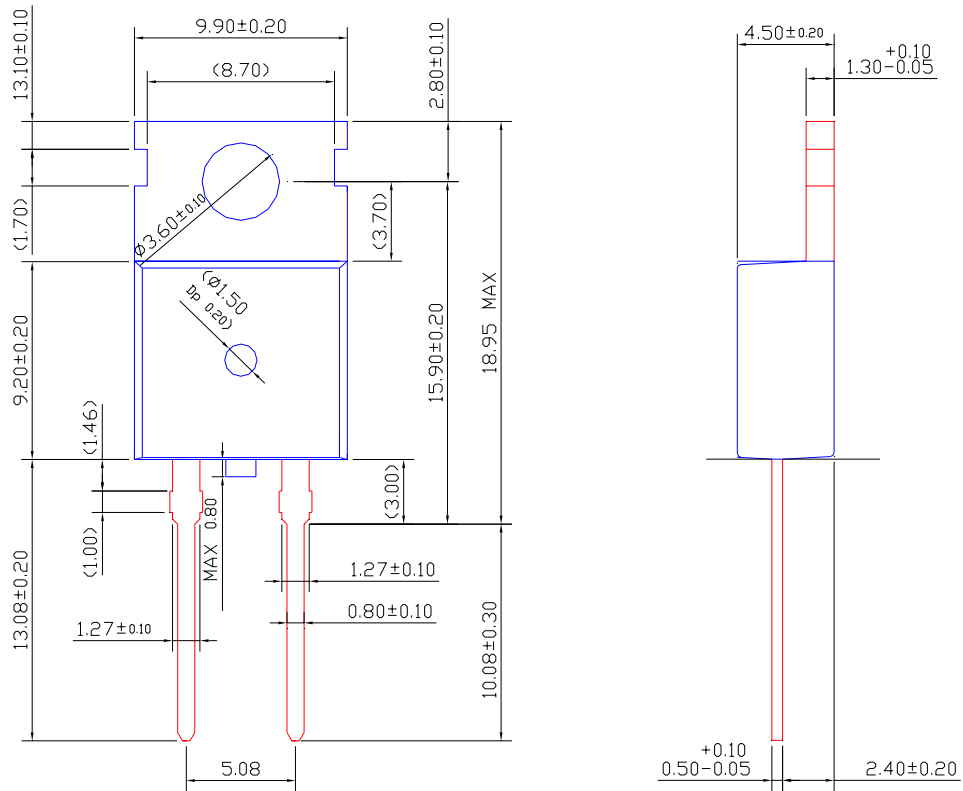


Figure 6. Forward Current Deration Curve



Mechanical Dimensions

TO-220-2L



NOTE

1. THESE DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION.
2. () IS REFERENCE
3. [] IS ASS'Y OUT QUALITY

Dimensions in Millimeters

